

Amendments to the Claims

Claims 1-15 (Cancelled).

16. (Previously Presented) A semiconductor structure for detecting completion of processing of a material, comprising: a sacrificial layer formed below the material, the sacrificial layer having a detectable condition, wherein the material comprises a liner for interconnects in a wiring level.

17. (Original) The semiconductor structure of claim 16, wherein the sacrificial layer comprises a fluorescent film, and wherein the detectable condition comprises fluorescence.

18. (Cancelled).

19. (Previously Presented) A semiconductor structure for detecting completion of processing of a material, comprising:

    a sacrificial layer formed below the material, the sacrificial layer having a detectable condition,

    wherein the sacrificial layer is selected from the group consisting of: europium thenoyltrifluoroacetone (EuTTA); chelates of La, Sm, Eu, Gd, Lu, Yb, Tb, Dy or Tm; and (beta)-diketone chelates including Eu benzoylacetone, Eu dibenzoylmethide or Eu hexafluoroacetone.

20. (Cancelled).